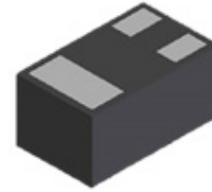
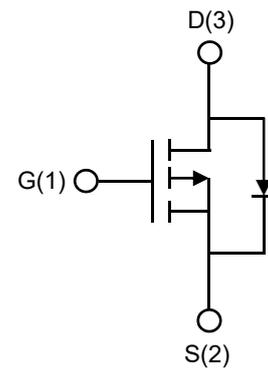
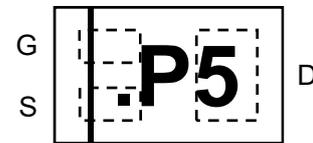


Description

The MOSFET provide the best combination of fast switching , low on-resistance and cost-effectiveness.


**DFN1006-3L
(Bottom View)**

Circuit Diagram

Marking (Top View)
MOSFET Product Summary

| $V_{DS}(V)$ | $R_{DS(on)}(m\Omega)$ | $I_D(A)$ |
|-------------|------------------------|----------|
| -20 | 130 @ $V_{GS} = -4.5V$ | -2 |
| | 160 @ $V_{GS} = -2.5V$ | |

Feature

- High Power and current handling capability
- Lead free product is acquired
- Surface Mount Package

Applications

- PWM applications
- Load switch
- Power management

Absolute maximum rating@25°C

| Rating | Symbol | Value | Units |
|--|----------------|----------|---------------|
| Drain-source Voltage | V_{DS} | -20 | V |
| Gate-source Voltage | V_{GS} | ± 12 | V |
| Drain Current | I_D | -2 | A |
| Pulsed Drain Current | I_{DP} | -6 | A |
| Total Power Dissipation | P_D | 270 | mW |
| Channel to ambient | $R_{th(ch-a)}$ | 420 | $^{\circ}C/W$ |
| Junction and Storage Temperature Range | T_J, T_{STG} | -55~+150 | $^{\circ}C$ |

Electrical characteristics per line@25°C (unless otherwise specified)

| Parameter | Symbol | Conditions | Min. | Typ. | Max. | Units |
|------------------------------------|--------------|--|-------|-------|-----------|------------|
| Off Characteristics | | | | | | |
| Drain-Source Breakdown Voltage | BV_{DSS} | $V_{GS} = 0V, I_D = -250\mu A$ | -20 | - | - | V |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{DS} = -20V, V_{GS} = 0V$ | - | - | -1 | μA |
| Gate-Body Leakage Current | I_{GSS} | $V_{GS} = \pm 12V, V_{DS} = 0V$ | - | - | ± 0.1 | μA |
| On Characteristics | | | | | | |
| Gate Threshold Voltage | $V_{GS(th)}$ | $V_{DS} = V_{GS}, I_D = -250\mu A$ | -0.45 | -0.55 | -0.85 | V |
| Static Drain-Source On-Resistance | $R_{DS(ON)}$ | $V_{GS} = -4.5V, I_D = -1.0A$ | - | 130 | 170 | m Ω |
| | | $V_{GS} = -2.5V, I_D = -1.0A$ | - | 160 | 190 | |
| Dynamic Parameters | | | | | | |
| Input Capacitance | C_{iss} | $V_{DS} = -10V, V_{GS} = 0V,$ $f = 1MHz$ | - | 248 | - | pF |
| Output Capacitance | C_{oss} | | - | 30 | - | |
| Reverse Transfer Capacitance | C_{rss} | | - | 28 | - | |
| Switching Parameters | | | | | | |
| Turn-on Delay Time | $t_{d(on)}$ | $V_{DS} = -10V, V_{GS} = -4.5V,$ $R_G = 6\Omega, I_D = 450mA$ | - | 5 | - | ns |
| Turn-on Rise Time | t_r | | - | 5 | - | |
| Turn-Off Delay Time | $t_{d(off)}$ | | - | 53 | - | |
| Turn-Off Fall Time | t_f | | - | 34 | - | |
| Total Gate Charge | Q_g | $V_{DS} = -10V, I_D = -450mA,$ $V_{GS} = -4.5V$ | - | 3.0 | - | nC |
| Gate-Source Charge | Q_{gs} | | - | 0.2 | - | |
| Gate-Drain Charge | Q_{gd} | | - | 0.8 | - | |
| Drain-Source Diode Characteristics | | | | | | |
| Diode Forward Voltage | V_{SD} | $V_{GS} = 0V, I_S = -1A$ | -0.5 | -0.85 | -1.1 | V |

Typical Characteristics

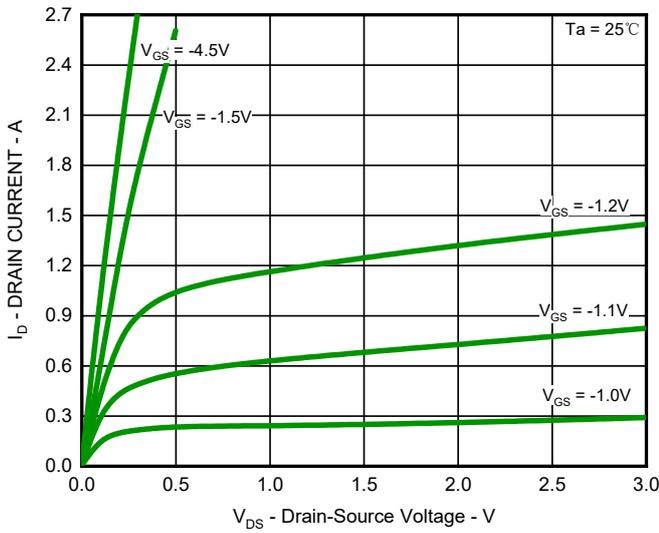


Fig.1 Output Characteristics

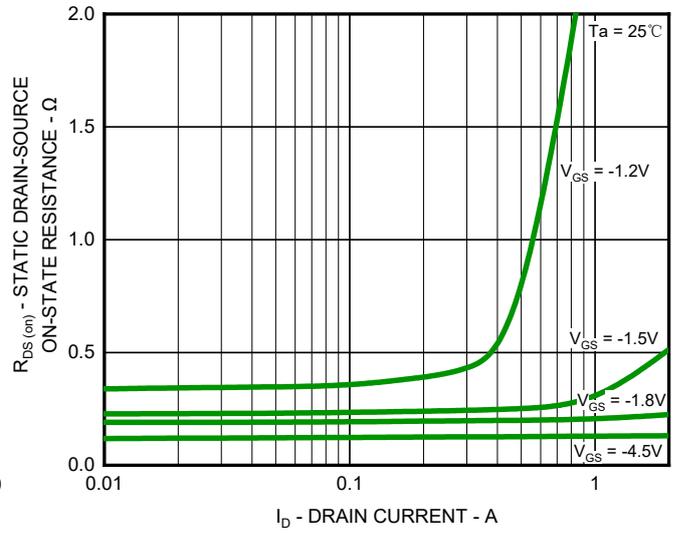


Fig.2 On-Resistance vs. Drain Current (I)

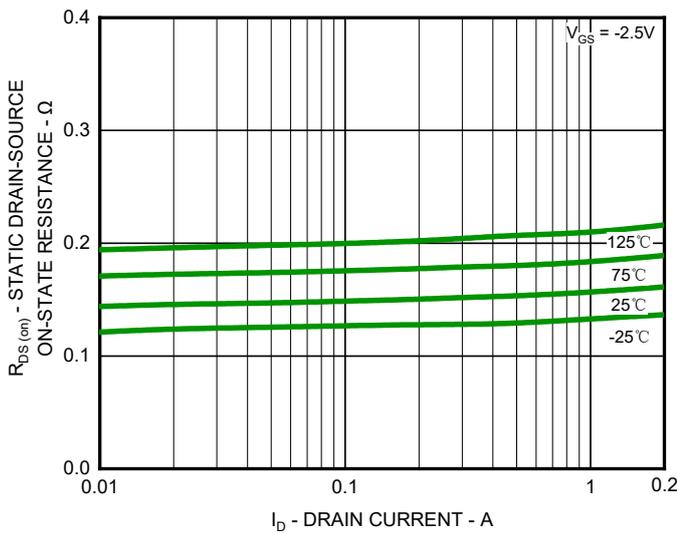


Fig.3 On-Resistance vs. Drain Current (II)

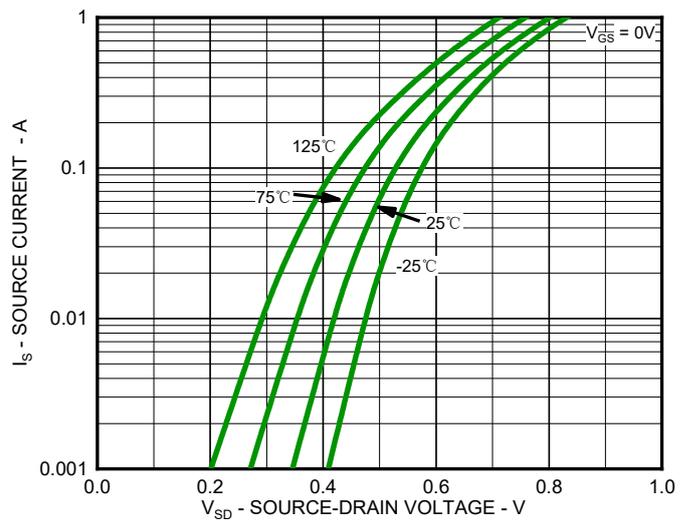


Fig.4 Diode Forward Voltage vs. Current

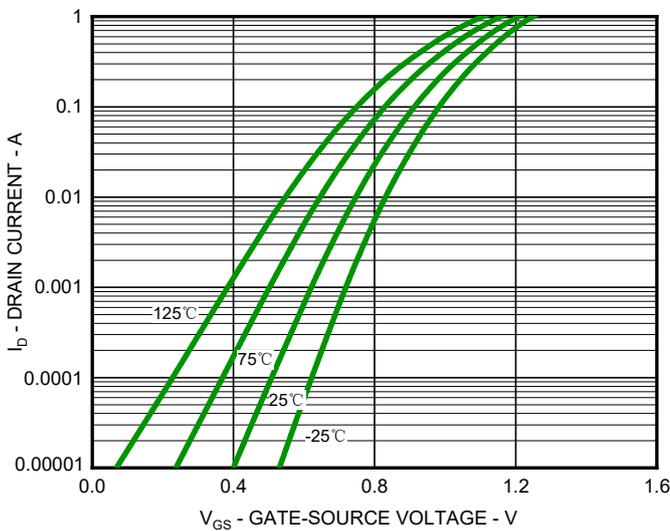


Fig.5 Typical Transfer Characteristic

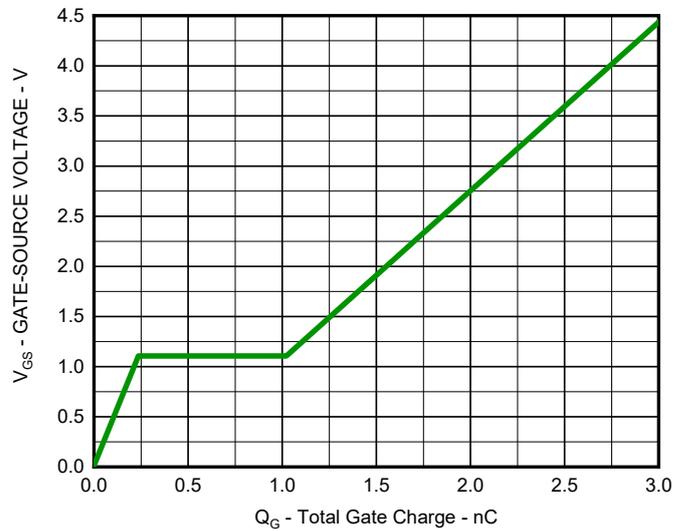


Fig.6 Gate Charge Characteristics

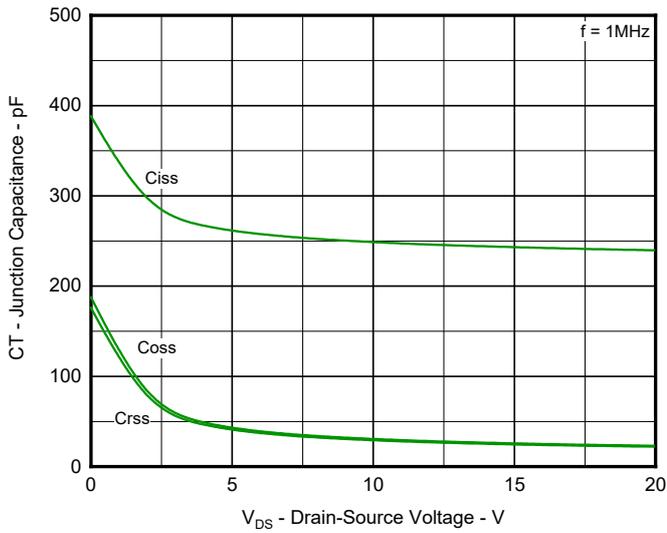


Fig.7 Typical Junction Capacitance

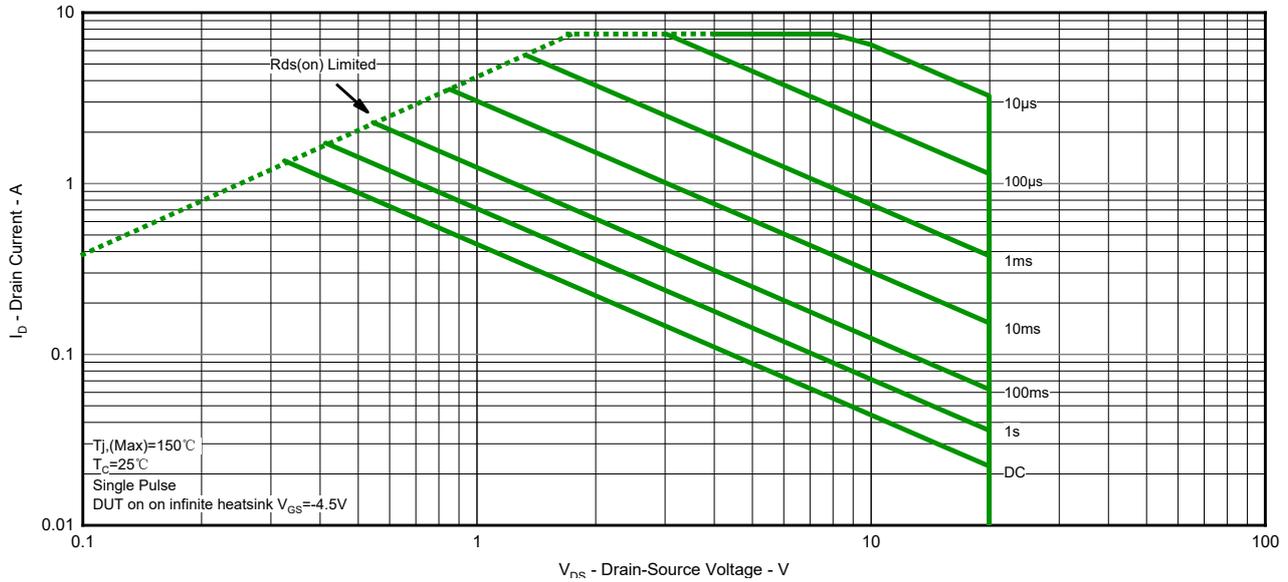


Fig.8 Safe Operation Area

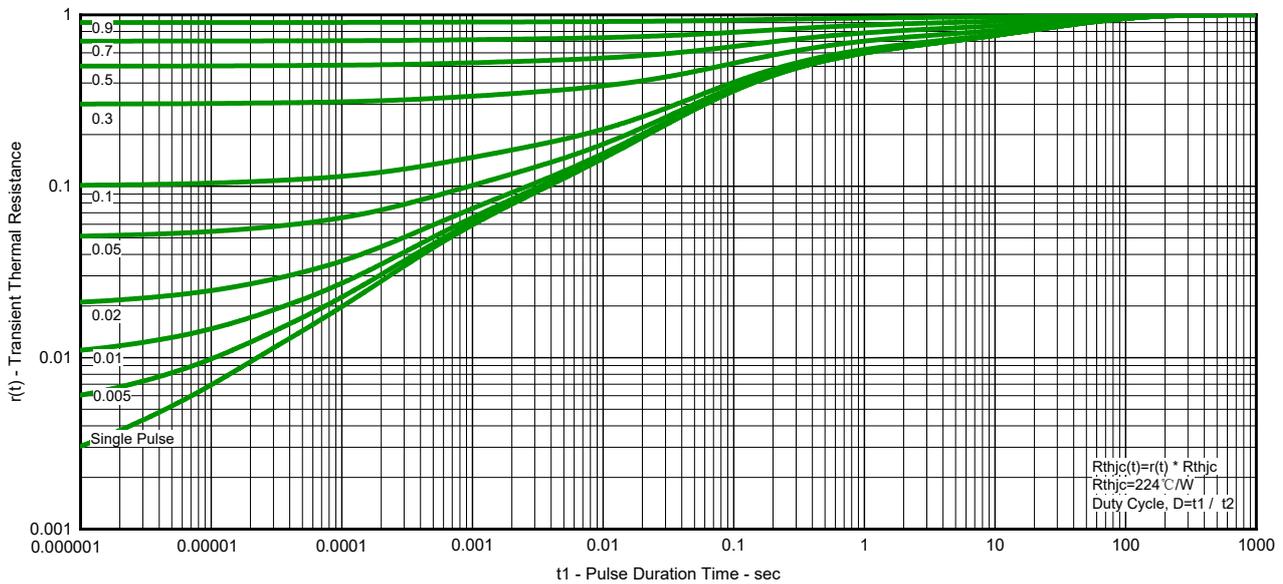
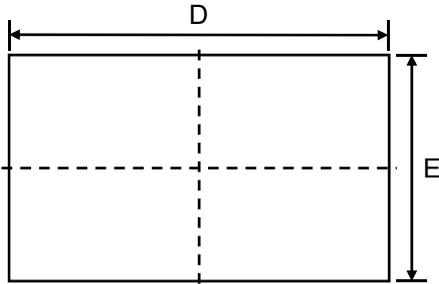
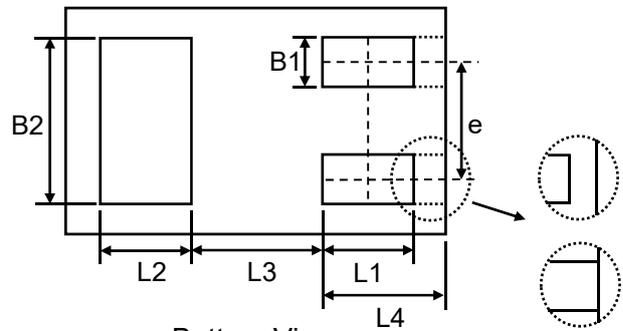


Fig.9 Transient Thermal Resistance

Product Dimension (DFN1006-3L)



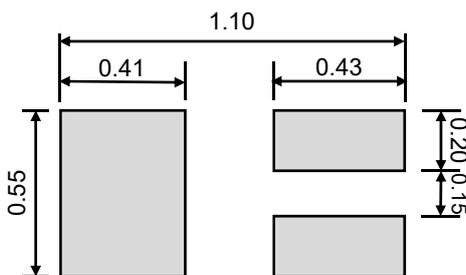
Top View



Bottom View



Side View



Suggested PCB Layout

| Dim | Millimeters | | Inches | |
|-----|-------------|------|--------|-------|
| | Min | Max | Min | Max |
| A | 0.33 | 0.55 | 0.013 | 0.022 |
| B | 0.00 | 0.05 | 0.000 | 0.002 |
| B1 | 0.10 | 0.20 | 0.004 | 0.008 |
| B2 | 0.45 | 0.55 | 0.018 | 0.022 |
| D | 0.90 | 1.05 | 0.035 | 0.041 |
| E | 0.50 | 0.65 | 0.020 | 0.026 |
| e | 0.35 | | 0.014 | |
| L1 | 0.20 | 0.30 | 0.008 | 0.012 |
| L2 | 0.20 | 0.30 | 0.008 | 0.012 |
| L3 | 0.39 | | 0.015 | |
| L4 | 0.25 | 0.35 | 0.010 | 0.014 |

Unit: mm

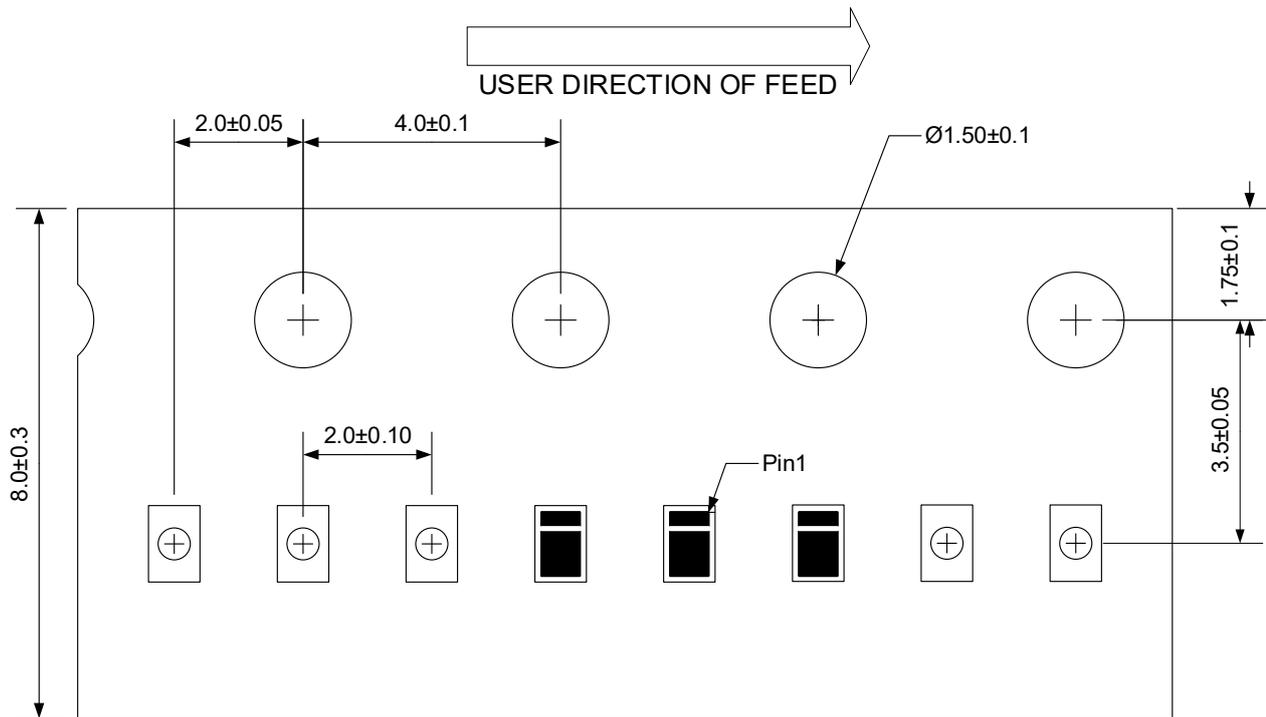
P-Channel MOSFET

PPM3FD20V2N

Ordering information

| Device | Package | Reel | Shipping |
|-------------|---------------------|------|---------------------|
| PPM3FD20V2N | DFN1006-3L(Pb-Free) | 7" | 10000 / Tape & Reel |

Load with information



Unit:mm

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